

Amendments to the Specification

Please replace the paragraph beginning on page 23, line 12, with the following rewritten paragraph:

An NPN lateral bipolar transistor 150 is formed by a collector 152 formed in the same N^+ diffusion region as the drain 114, an emitter formed by the N^+ region 154 (hereinafter may be called emitter 154), and a base contact formed by the P^+ region 156 connected to the P-type well (hereinafter may be called base contact 156). Fig. 1 shows a contact 158 connected to the emitter 154 and a contact 159 connected to the base contact 156, both of which are grounded.